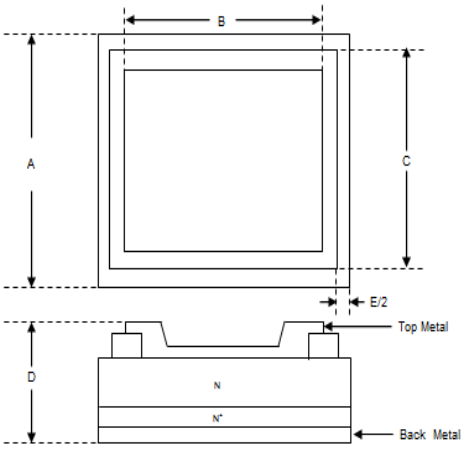
# TSB82T100S(A)S-255A

## 10A/100V(1), low VF Schottky barrier diode with trench MOS structure

## Mechanical Data

| Chip Drawing | Item | Information | |
|---|---|---|---|
|  | Die Size (A) | 2082 µm | 82 mil |
| | Top Metal Pad Size (B) | 1950µm | 77mil |
| | Chip Size (C) | 2002µm | 79mil |
| | Wafer Thickness (D) | 255 µm | 9.5 mil |
| | Scribe Line Width (E) | 80 µm | 3.15 mil |
| | Wafer Size | 6 inch | |
| | Top Side Metallization | Al/Ag | |
| | Back Side Metallization | Ti Ni Ag | |
| | Recommended Storage Environment | Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23 ±3 ) | |

## Electrical Characteristics ($T_J$=25℃, unless otherwise specified)(2)

| Parameter | Description | Min. | Typ. | Max. | Unit | Test Condition |
|---|---|---|---|---|---|---|
| $V_{BR}$ | Reverse Breakdown Voltage | 105 | 109 | - | V | $I_R$ =100µA |
| $V_F$ | Instantaneous Forward Voltage | - | 0.53 | 0.59 | V | $I_F$ =5A(3) |
| | | - | 0.67 | 0.70 | V | $I_F$ =10A(3) |
| $I_R$ | Reverse Leakage Current | - | 22 | 50 | | $V_R$ =105V |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature | -40 to 150 Max | | | | |

**Note:**

(1) The preliminary wafer datasheet only for reference;

(2) This characteristics assume the dies are assembled in SMC packages. Actual performance may degrade when assembled. YJ does not guarantee device performance after assembly;

(3) ;